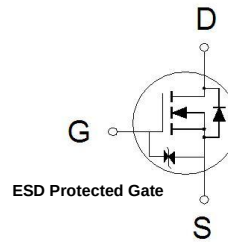


PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
80V	2.8m Ω	145A

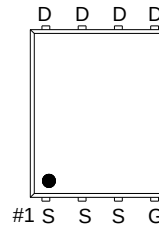


Features

- Pb-Free, Halogen Free and RoHS compliant.
- Low $R_{DS(on)}$ to Minimize Conduction Losses.
- Ohmic Region Good $R_{DS(on)}$ Ratio.
- Optimized Gate Charge to Minimize Switching Losses.
- Products Integrated ESD diode with ESD Protected.
- 100% UIS Tested & Rg Tested.

Applications

- Protection Circuits Applications.
- Computer for DC to DC Converters Applications.



G. GATE
D. DRAIN
S. SOURCE

100% UIS Tested
100% Rg Tested

ABSOLUTE MAXIMUM RATINGS ($T_A = 25\text{ }^{\circ}\text{C}$ Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Drain-Source Voltage		V_{DS}	80	V
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current ⁴	$T_C = 25\text{ }^{\circ}\text{C}$	I_D	145	A
	$T_C = 100\text{ }^{\circ}\text{C}$		92	
Pulsed Drain Current ¹		I_{DM}	194	
Continuous Drain Current	$T_A = 25\text{ }^{\circ}\text{C}$	I_D	30	
	$T_A = 70\text{ }^{\circ}\text{C}$		24	
Avalanche Current		I_{AS}	75	
Avalanche Energy	$L = 0.1\text{mH}$	E_{AS}	281	mJ
Power Dissipation	$T_C = 25\text{ }^{\circ}\text{C}$	P_D	114	W
	$T_C = 100\text{ }^{\circ}\text{C}$		45	
Power Dissipation ³	$T_A = 25\text{ }^{\circ}\text{C}$	P_D	5	W
	$T_A = 70\text{ }^{\circ}\text{C}$		3.2	
Operating Junction & Storage Temperature Range		T_j, T_{stg}	-55 to 150	$^{\circ}\text{C}$

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE		SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Ambient ²	$t \leq 10s$	$R_{\theta JA}$		25	°C / W
Junction-to-Ambient ²	Steady-State	$R_{\theta JA}$		45	
Junction-to-Case	Steady-State	$R_{\theta JC}$		1.1	

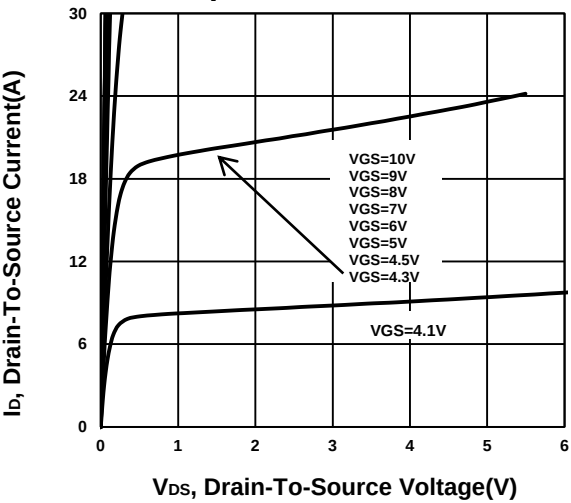
¹Pulse width limited by maximum junction temperature.²The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ\text{C}$.³The Power dissipation is based on $R_{\theta JA}$ $t \leq 10s$ value.⁴The maximum current rating is package limited.ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	80			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	2	2.9	4	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 20V$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 80V, V_{GS} = 0V$			1	μA
		$V_{DS} = 80V, V_{GS} = 0V, T_J = 55^\circ C$			10	
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS} = 10V, I_D = 20A$		2.2	2.8	m Ω
Forward Transconductance	g_{fs}	$V_{DS} = 5V, I_D = 20A$		77		S
DYNAMIC						
Input Capacitance	C_{iss}	$V_{GS} = 0V, V_{DS} = 50V, f = 300kHz$		7042		pF
Output Capacitance	C_{oss}			973		
Reverse Transfer Capacitance	C_{rss}			7.4		
Gate Resistance	R_g	$f = 1MHz$		1.7		Ω
Total Gate Charge ⁵	Q_g	$V_{DS} = 40V, V_{GS} = 10V, I_D = 20A$		97		nC
Gate-Source Charge ⁵	Q_{gs}			33		
Gate-Drain Charge ⁵	Q_{gd}			13		
Turn-On Delay Time ⁵	$t_{d(on)}$	$V_{DS} = 40V, I_D \cong 20A, V_{GS} = 10V, R_{GEN} = 6\Omega$		31		nS
Rise Time ⁵	t_r			60		
Turn-Off Delay Time ⁵	$t_{d(off)}$			83		
Fall Time ⁵	t_f			65		

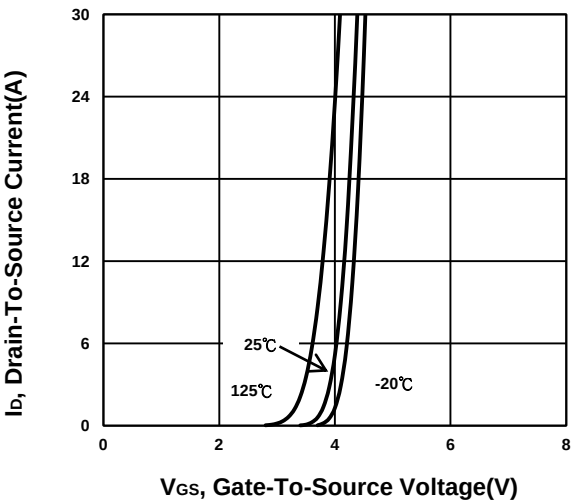
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T _J = 25 °C)						
Continuous Current ⁶	I _S				95	A
Forward Voltage	V _{SD}	I _F = 20A, V _{GS} = 0V			1.2	V
Reverse Recovery Time	t _{rr}	I _F = 20A, dI _F /dt = 100A / μS		66		nS
Reverse Recovery Charge	Q _{rr}			92		nC

⁵Independent of operating temperature.
⁶The maximum current rating is package limited.

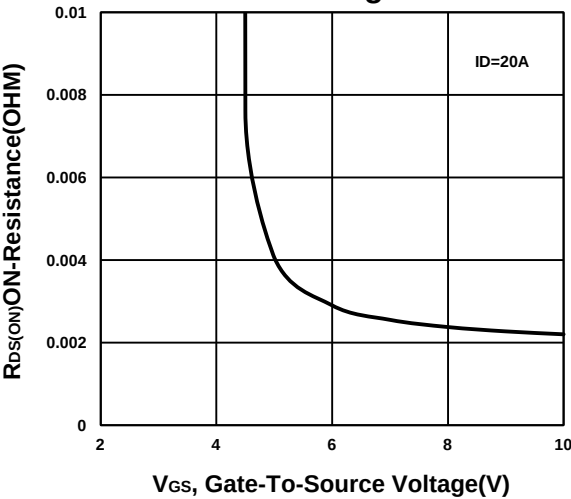
Output Characteristics



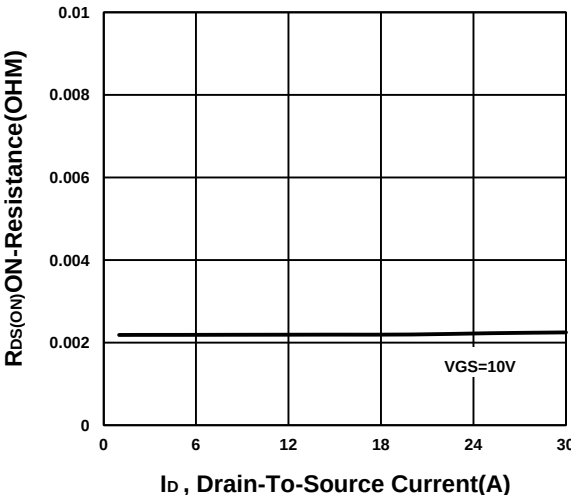
Transfer Characteristics



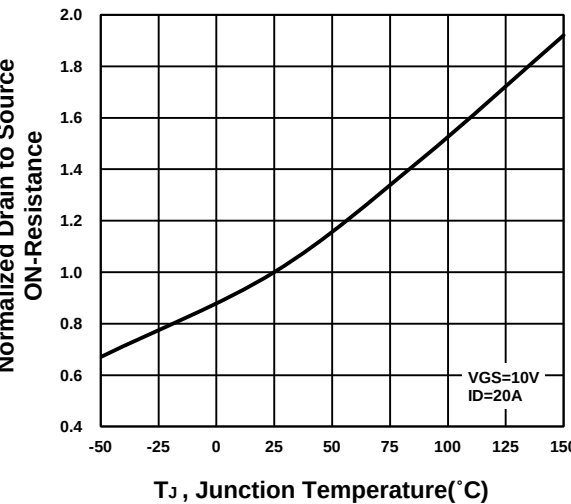
On-Resistance VS Gate-To-Source Voltage



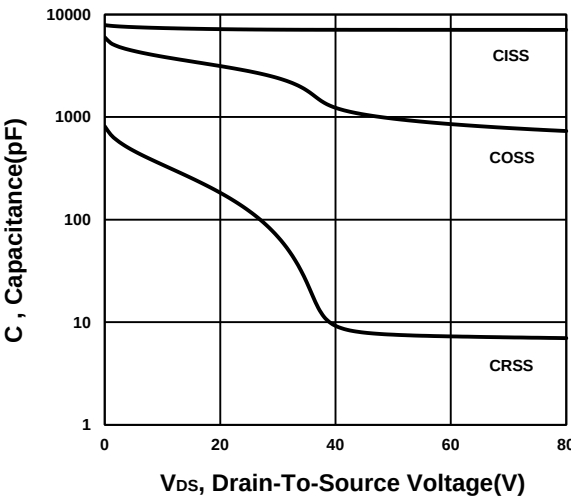
On-Resistance VS Drain Current



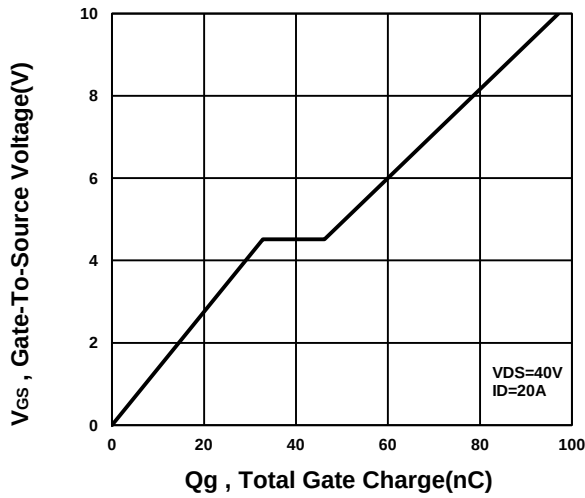
On-Resistance VS Temperature



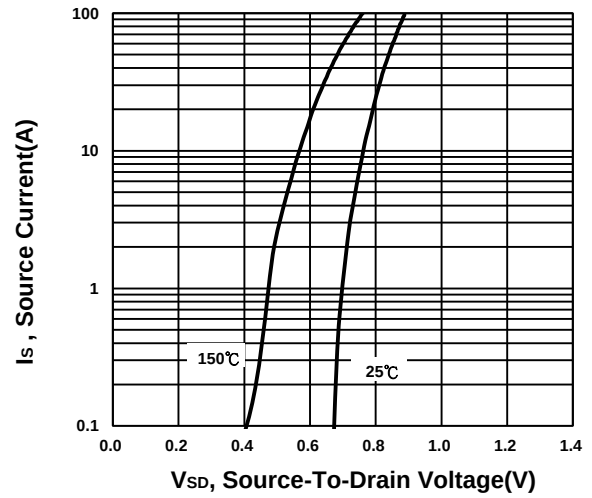
Capacitance Characteristic



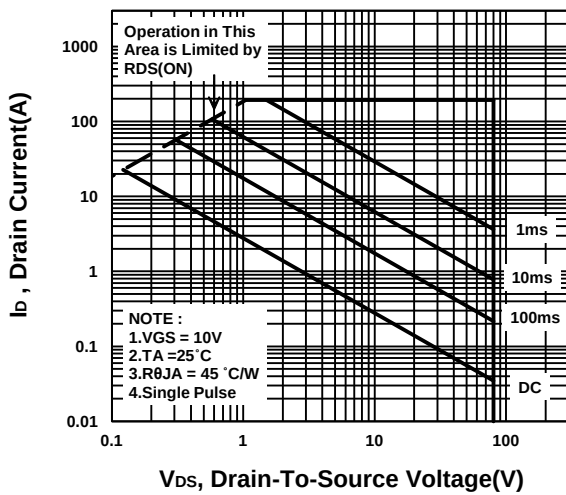
Gate charge Characteristics



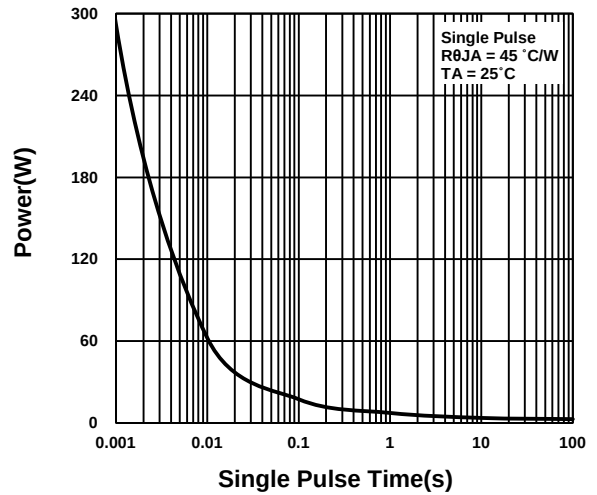
Source-Drain Diode Forward Voltage



Safe Operating Area



Single Pulse Maximum Power Dissipation



Transient Thermal Response Curve

